CRMKTU0305A

Description

N-channel Enhancement Mode Power MOSFET

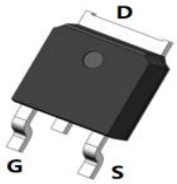
Features

- 25V, 90A
  $R_{DS(ON)}$ Typ= 3mΩ @ V_{GS} = 4.5V
  $R_{DS(ON)}$ Typ= 4mΩ @ V_{GS} = 2.5V
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge

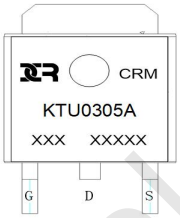
Applications

- Load Switch
- PWM Application
- Power Management

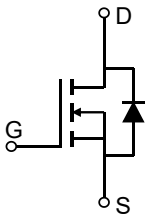
100% UIS TESTED!
100% ΔVds TESTED!



TO-252-3L



Marking and Pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Outline	Package	Reel Size	Reel(pcs)	Per Carton (pcs)
CRMKTU0305A	CRMKTU0305A	TAPING	TO-252-3L	13"	2500	25000

Absolute Maximum Ratings (@ T_J = 25°C unless otherwise specified)

Symbol	Parameter		Value	Units
V_{DS}	Drain-to-Source Voltage		25	V
V_{GS}	Gate-to-Source Voltage		±12	V
I_D	Continuous Drain Current	T_C = 25°C	90	A
		T_C = 100°C	54	
I_{DM}	Pulsed Drain Current (1)		360	A
E_{AS}	Single Pulsed Avalanche Energy (2)		132	mJ
P_D	Power Dissipation	T_C = 25°C	54	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		2.3	°C/W
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	°C

Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	25	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 25V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±12V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	0.4	0.8	1.2	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(3)	V_{GS} = 4.5V, I_D = 20A	-	3.0	3.9	mΩ
		V_{GS} = 2.5V, I_D = 10A	-	4.0	5.2	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 10V, f = 1MHz	-	3280	-	pF
C_{oss}	Output Capacitance		-	362	-	pF
C_{rss}	Reverse Transfer Capacitance		-	298	-	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 10V V_{DS} = 15V, I_D = 30A	-	42	-	nC
Q_{gs}	Gate Source Charge		-	9	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	10	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = 10V, V_{DD} = 15V I_D= 30A, R_{GEN} = 3Ω	-	9	-	ns
t_r	Turn-On Rise Time		-	15	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	36	-	ns
t_f	Turn-Off Fall Time		-	11	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	90	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	360	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S = 30A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I_F = 20A, di/dt = 100A/us	-	11	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	2.5	-	nC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.

2. E_{AS} condition: Starting T_J=25C, V_{DD}=10V, V_G=10V, R_G=25ohm, L=0.5mH, I_{AS}=23A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

Test Circuit

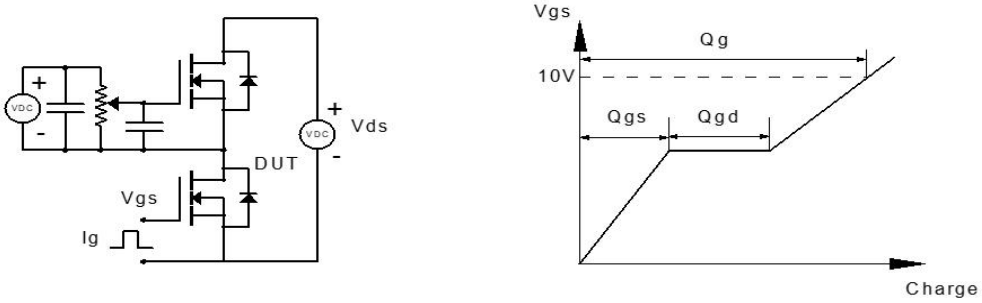


Figure 1: Gate Charge Test Circuit & Waveform

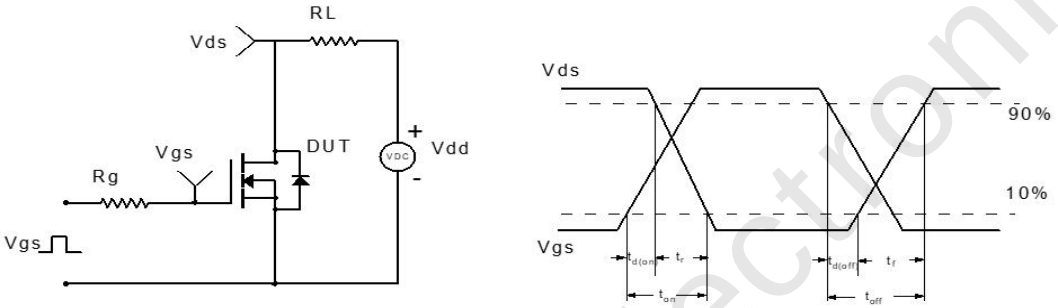


Figure 2: Resistive Switching Test Circuit & Waveform

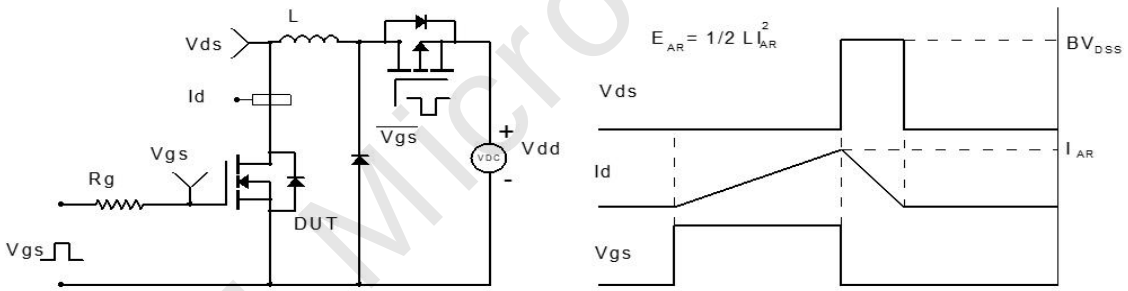


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

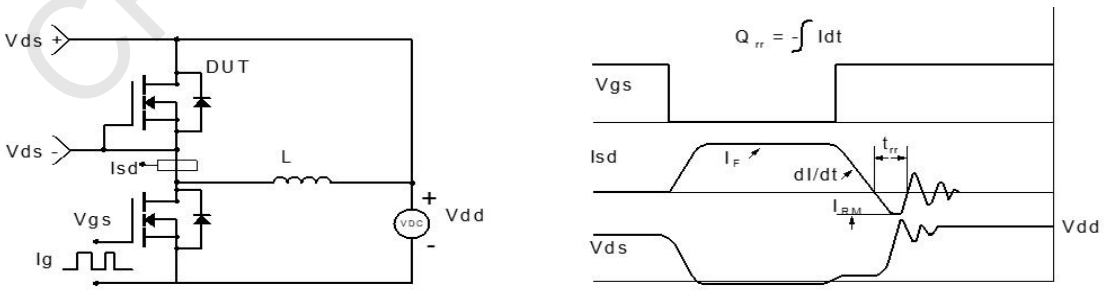
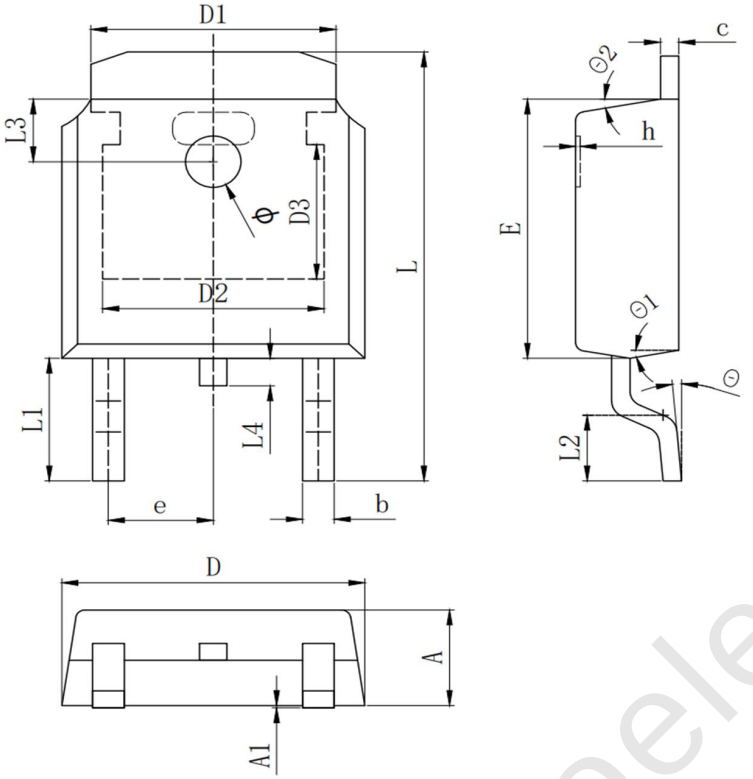


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(TO-252-3L)



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	2.200	2.300	2.400
A1	0.000		0.127
b	0.640	0.690	0.740
c(电镀后)	0.460	0.520	0.580
D	6.500	6.600	6.700
D1	5.334 REF		
D2	4.826 REF		
D3	3.166 REF		
E	6.000	6.100	6.200
e	2.286 TYP		
h	0.000	0.100	0.200
L	9.900	10.100	10.300
L1	2.888 REF		
L2	1.400	1.550	1.700
L3	1.600 REF		
L4	0.600	0.800	1.000
Φ	1.100	1.200	1.300
θ	0°		8°
θ1	9° TYP		
θ2	9° TYP		